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Keywords: vitriform films, method sol-gel, porous matrixes

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Keywords: nanostructured solid solution, photocatalyst, water photolysis, irradiance of incident light

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Keywords: graphene, properties of graphene, methods of obtaining graphene, industrial production of graphene

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Keywords: X-ray structure analysis, solid solutions, oxygen-octahedral structures, reconstructive phase transitions

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Keywords: microsystem technics, bending rigidity of an executive element, deformation, measuring dynamic indentation, dependence "loading-deformation"

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Keywords: quantum, laser, quantum dot

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Keywords: biosensor, suspended SiNWs, sensor sensitivity, Si-NW FET, CMOS technology

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Keywords: bank, pitch, angular velocity, acceleration, micromechanical accelerometer, micromechanical gyroscope

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